

2SK2734

Silicon N Channel MOS FET
High Speed Power Switching

HITACHI

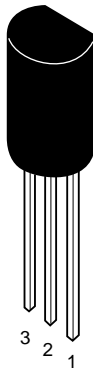
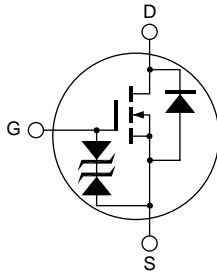
ADE-208-520
1st. Edition

Features

- Low on-resistance
 $R_{DS(on)} = 0.04\Omega$ typ (at $V_{GS} = 10\text{ V}$, $I_D = 2.5\text{ A}$)
- 4V gate drive devices.
- Large current capacitance
 $I_D = 5\text{ A}$

Outline

TO-92MOD.



1. Source
2. Drain
3. Gate

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	5	A
Drain peak current	$I_{D(pulse)}^{*1}$	20	A
Body to drain diode reverse drain current	I_{DR}	5	A
Channel dissipation	Pch	0.9	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

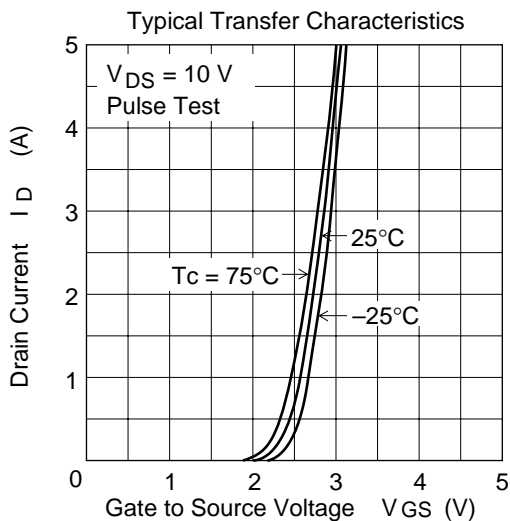
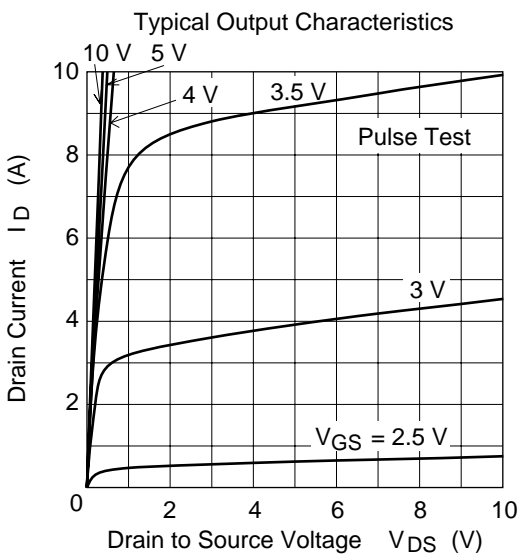
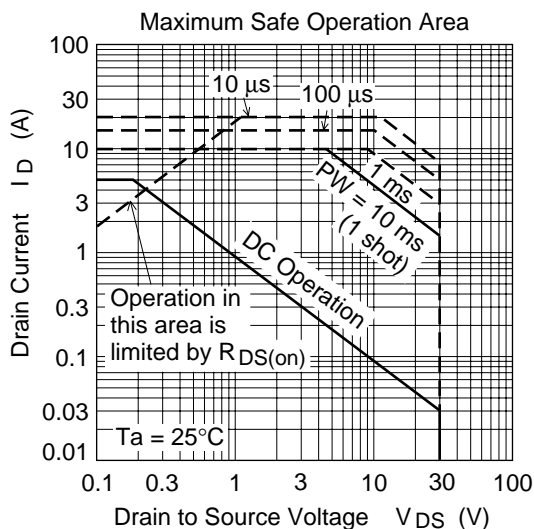
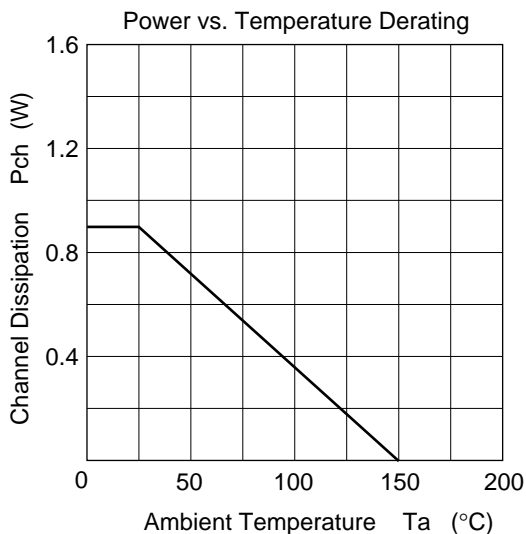
Note: 1. $PW \leq 10\mu s$, duty cycle $\leq 1\%$

Electrical Characteristics (Ta = 25°C)

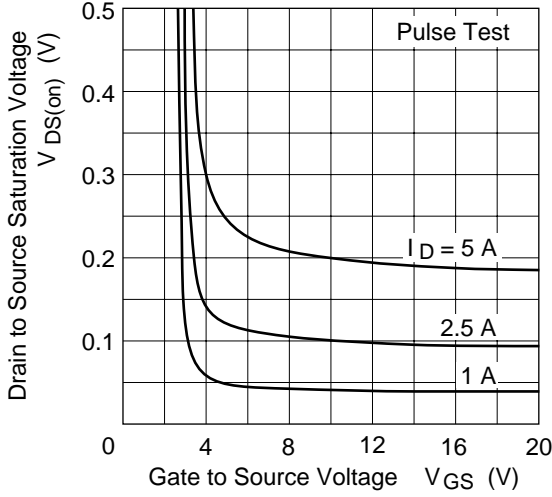
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 10mA, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100\mu A, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 30V, V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16V, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1mA, V_{DS} = 10V$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.04	0.055	Ω	$I_D = 2.5A, V_{GS} = 10V^{*1}$
	$R_{DS(on)}$	—	0.055	0.08	Ω	$I_D = 2.5A, V_{GS} = 4V^{*1}$
Forward transfer admittance	$ y_{fs} $	4	7	—	S	$I_D = 2.5A, V_{DS} = 10V^{*1}$
Input capacitance	Ciss	—	550	—	pF	$V_{DS} = 10V$
Output capacitance	Coss	—	380	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	155	—	pF	f = 1MHz
Turn-on delay time	$t_{d(on)}$	—	14	—	ns	$V_{GS} = 10V, I_D = 2.5A$
Rise time	t_r	—	80	—	ns	$R_L = 4\Omega$
Turn-off delay time	$t_{d(off)}$	—	80	—	ns	
Fall time	t_f	—	65	—	ns	
Body to drain diode forward voltage	V_{DF}	—	1.0	—	V	$I_F = 5A, V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	40	—	ns	$I_F = 5A, V_{GS} = 0$ $di_F/dt = 50A/\mu s$

Note: 1. Pulse test

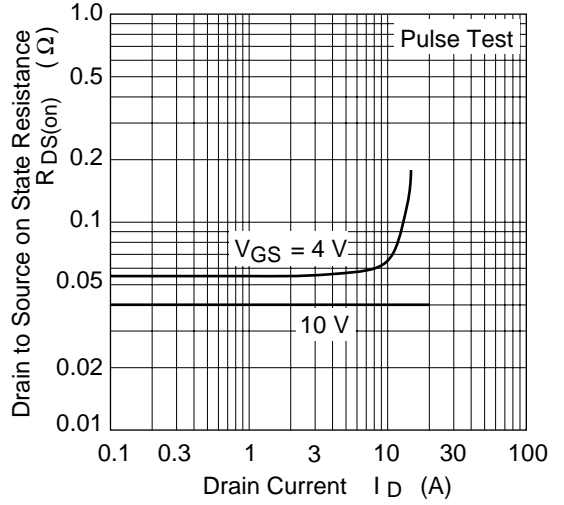
Main Characteristics



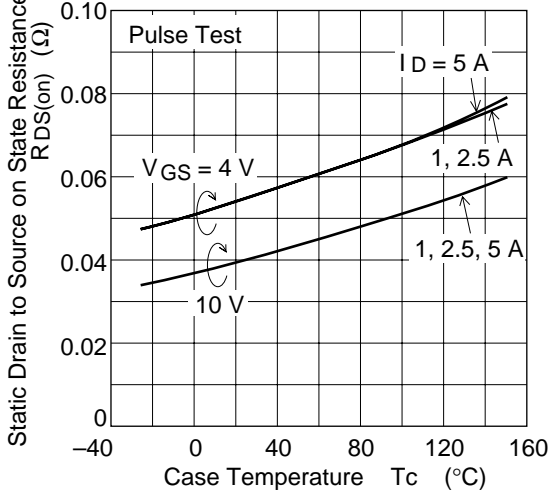
Drain to Source Saturation Voltage vs. Gate to Source Voltage



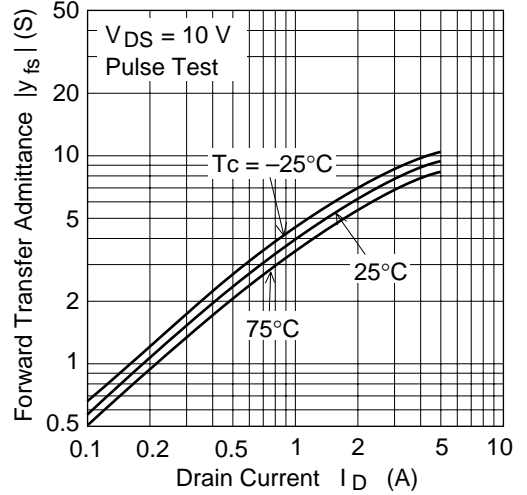
Static Drain to Source on State Resistance vs. Drain Current



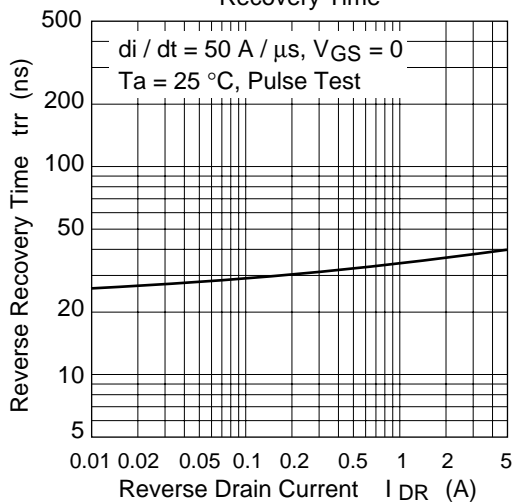
Static Drain to Source on State Resistance vs. Temperature



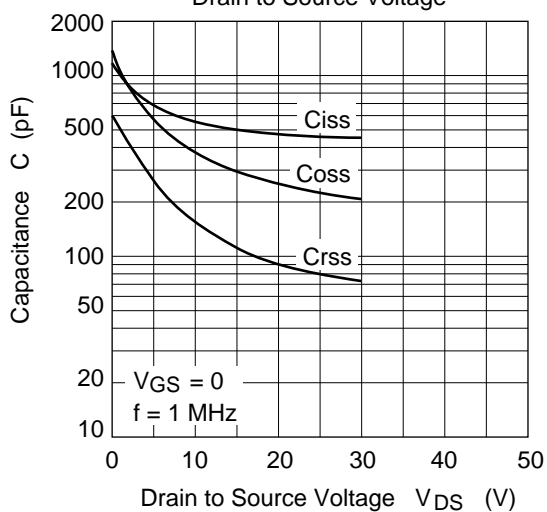
Forward Transfer Admittance vs. Drain Current



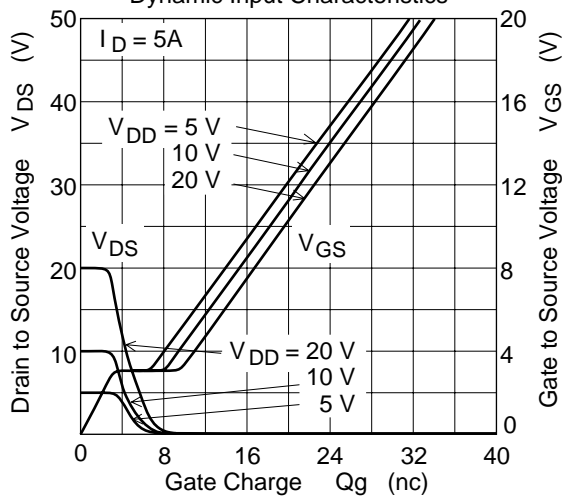
Body to Drain Diode Reverse Recovery Time



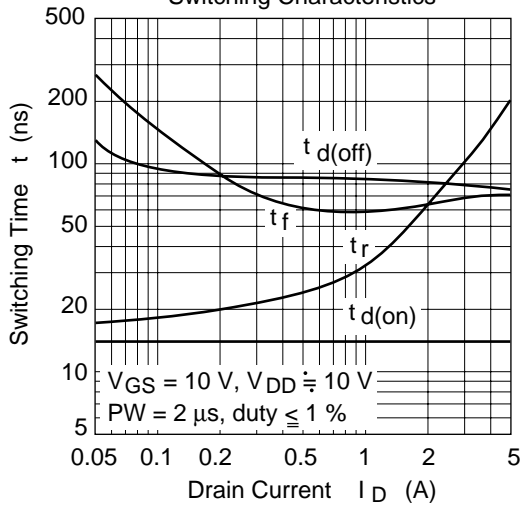
Typical Capacitance vs. Drain to Source Voltage

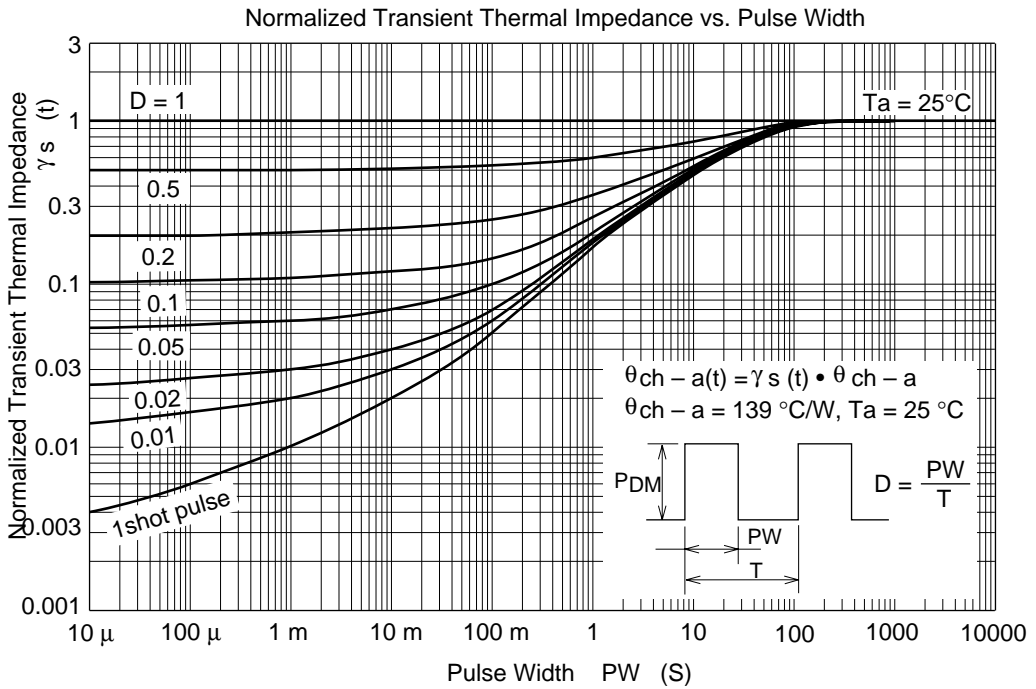
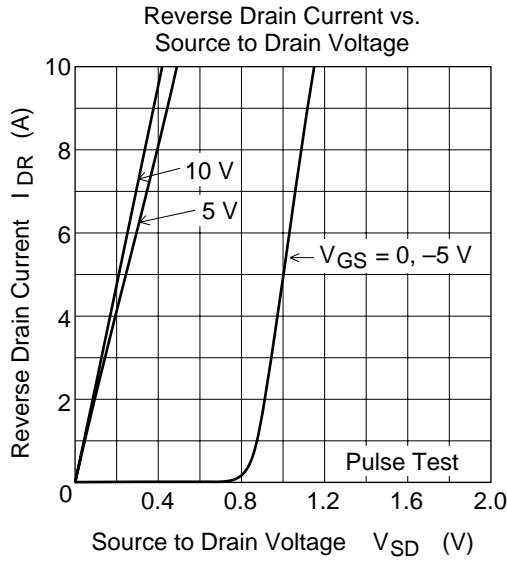


Dynamic Input Characteristics

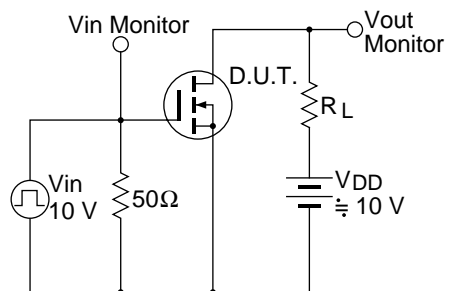


Switching Characteristics

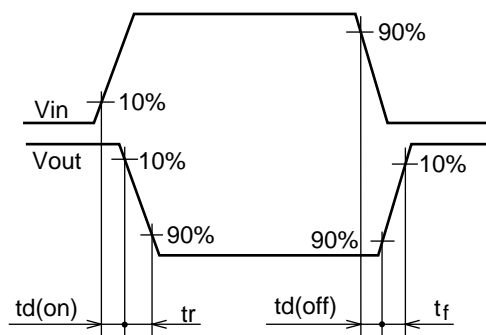




Switching Time Test Circuit

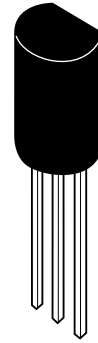
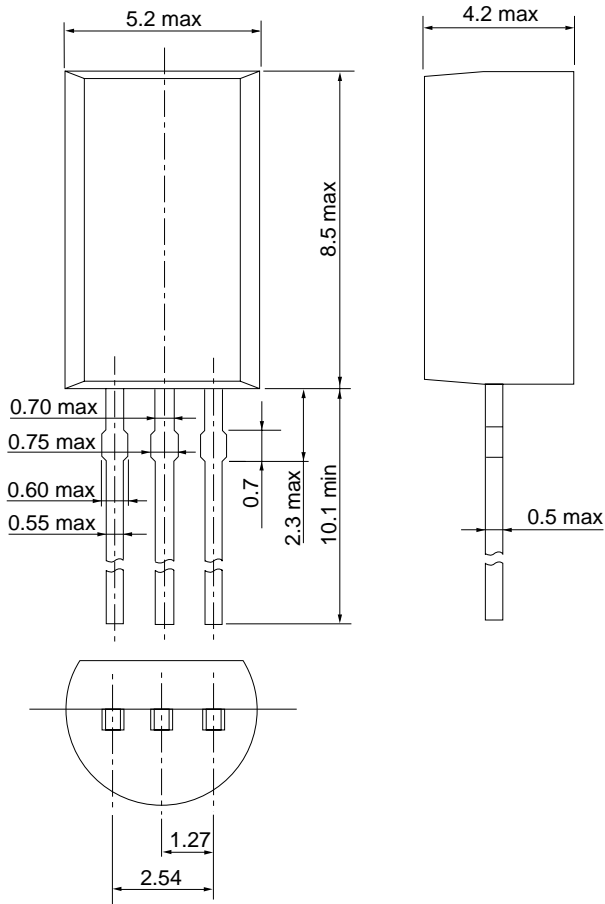


Switching Time Waveforms



Package Dimentions

Unit: mm



Hitachi Code	TO-92Mod.
EIAJ	SC-51
JEDEC	—

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